

Monday, September 2

**Short Courses (ES024, ES025)
Satellite Workshop
Laboratory Tour
17:30-19:00 Welcome Reception (ES Building)**

Tuesday, September 3

9:00-12:45 Opening & Plenary Sessions (Toyoda Auditorium)

ES Meeting Room	ES021	ES022	ES024	ES025	ES033	ES034	IB011	IB013	IB014	IB015	IB Lecture Hall
14:00-15:30 A-1:Organic and Hybrid Electronics	14:15-15:15 B-1:Hybrid Photonic Devices	14:00-15:30 C-1:Thermoelectric Devices	14:00-15:30 D-1:Synthesis & Characterization of 2D Materials	14:00-15:30 E-1:Quantum Information Engineering I	14:00-15:30 F-1:Advanced Characterization Techniques	14:00-15:30 G-1:Oxide Device and Integration	14:00-15:30 H-1:ReRAM	14:00-15:45 J-1:Advanced Interconnects	14:00-15:30 K-1:GaN Power Devices	14:00-15:15 M-1:Information Sensing Platform for IoT	14:00-15:30 N-1: Advanced CMOS Technology
Coffee Break											
15:45-17:30 A-2:Fabrication for Organic Devices	15:45-17:30 B-2:Photonic Integrated Circuits	15:45-17:30 C-2:Perovskite/Organic Solar Cell	15:45-17:15 D-2:Nanowires	15:45-17:30 E-2:Quantum Information Engineering II	15:45-17:30 F-2:GaN-Related Technologies	15:45-17:30 G-2:Crystal Growth of Group 4	15:45-17:30 H-2:Novel Approach to Polarization-Based Devices	15:45-16:45 J-2:3D Integration I		15:45-17:45 Area4 & Special M-2:Power Electronics for Smart Society	15:45-17:30 N-2:Emerging Semiconductor Materials: SiGe, Ge, and GaN

19:00-21:00 Banquet (Hotel Nagoya Castle)

Wednesday, September 4

ES Meeting Room	ES021	ES022	ES024	ES025	ES033	ES034	IB011	IB013	IB014	IB015	IB Lecture Hall
9:00-10:30 A-3:Biochemical Sensors	9:30-10:30 B-3: LiDAR	9:00-10:30 C-3:Battery/Fuel Cell/Capacitor	9:00-10:30 D-3:Physics & Application of Graphene Devices				9:00-10:30 H-3:Ferroelectric FET for Non-Volatile Device Applications		9:00-10:30 K-3:Si Power Technologies	9:00-10:30 Area1 & 3 & Special M-3:Advanced Integration Technologies	9:00-10:30 N-3:Steep Slope Transistor
Coffee Break											
10:45-11:30 Short Presentation Area7	10:45-11:30 Short Presentation Area5	10:45-11:30 Short Presentation Area6	10:45-11:30 Short Presentation Area8	10:45-11:30 Short Presentation Area9	10:45-11:30 Short Presentation Area11	10:45-11:30 Short Presentation Area10	10:45-11:30 Short Presentation Area2	10:45-11:30 Short Presentation Area3	10:45-11:30 Short Presentation Area4	10:45-11:30 Short Presentation Special	10:45-11:30 Short Presentation Area1

Luncheon Seminar:

13:00-15:00 Poster Session (Toyoda Auditorium)

Coffee Break											
15:30-16:30 A-4:Biophotonic Devices		15:30-16:30 C-4:Energy Harvesting	15:30-16:30 D-4:2D Materials & Devices I	15:30-16:30 E-4:Novel Functional Devices	15:30-16:30 F-4:2D Materials	15:30-16:30 G-4:Advanced Fabrication Technologies			15:30-16:45 K-4:GaN High Frequency Devices	15:30-16:45 Area2 & Special M-4:Advanced Memory Systems	15:30-16:30 N-4:3D and Stacking Technology
Coffee Break											

17:00-18:30 Rump Sessions

Thursday, September 5

ES Meeting Room	ES021	ES022	ES024	ES025	ES033	ES034	IB011	IB013	IB014	IB015	IB Lecture Hall
9:00-10:15 A-5: Sensor and Application	9:00-10:15 B-5:Photonic Devices Based on Novel Materials	9:00-10:15 C-5:Compound Solar Cell	9:00-10:15 D-5:Nanodevices	9:00-10:15 E-5:Spintronics I	9:00-10:15 F-5:Growth Mechanism of III-V Materials	9:00-10:15 G-5:Oxide Process and Applications	9:00-10:15 H-5:Memory Computing and MTP	9:00-10:15 J-5:3D Integration II	9:00-10:15 K-5:Wide-Bandgap Device Processing	9:00-10:15 M-5:Low Power and High Efficiency Circuits	9:00-10:15 N-5:Process Science and Technology
Coffee Break											
10:30-12:00 A-6:Transistors and Applications	10:30-11:45 B-6:III-V Photonic Devices	10:30-12:00 C-6:Silicon Solar Cell	10:30-12:00 D-6:2D Materials & Devices II	10:30-12:00 E-6:Spintronics II	10:30-12:00 F-6:Group IV Materials	10:30-12:00 G-6:Novel Thin Film Materials	10:30-11:45 H-6:Nonvolatile Memory Computing	10:30-12:00 J-6:Compound Semiconductors and Printing Technologies	10:30-12:00 K-6:SiC MOS Interface	10:30-12:00 M-6:Energy Efficient Systems and Components	10:30-12:00 N-6:Device Reliability and Parasitics
Lunch											
							13:00-14:30 H-7:MRAM, PCRAM and Emerging Memories		13:00-14:30 K-7:GaN Device Technologies	13:00-14:15 Area5 & 7 & Special M-7:Innovative Sensing Systems	13:00-14:30 Area1 & 9 N-7: Novel Approach to Polarization-Based Devices

Area Scope

- Area 1: Advanced CMOS: Material Fundamentals, Process Science and Device Physics
- Area 2: Advanced / Emerging Memories and New Applications
- Area 3: Interconnect / 3D Integrations / MEMS
- Area 4: Power Devices / High-speed Devices, and Materials
- Area 5: Photonics: Devices, Integration and Related Technology
- Area 6: Photovoltaic / Energy Harvesting / Battery-related Technology

Area Scope

- Area 7: Organic / Molecular / Bio-electronics
- Area 8: Low Dimensional Devices and Materials
- Area 9: Novel Functional / Quantum / Spintronic Devices and Materials
- Area 10: Thin Film Electronics: Oxide, Non-single Crystalline and Novel Process
- Area 11: Advanced Materials Synthesis, Crystal Growth and Characterization
- Special: Advanced Circuits/Systems Interacting with Innovative Devices & Material